

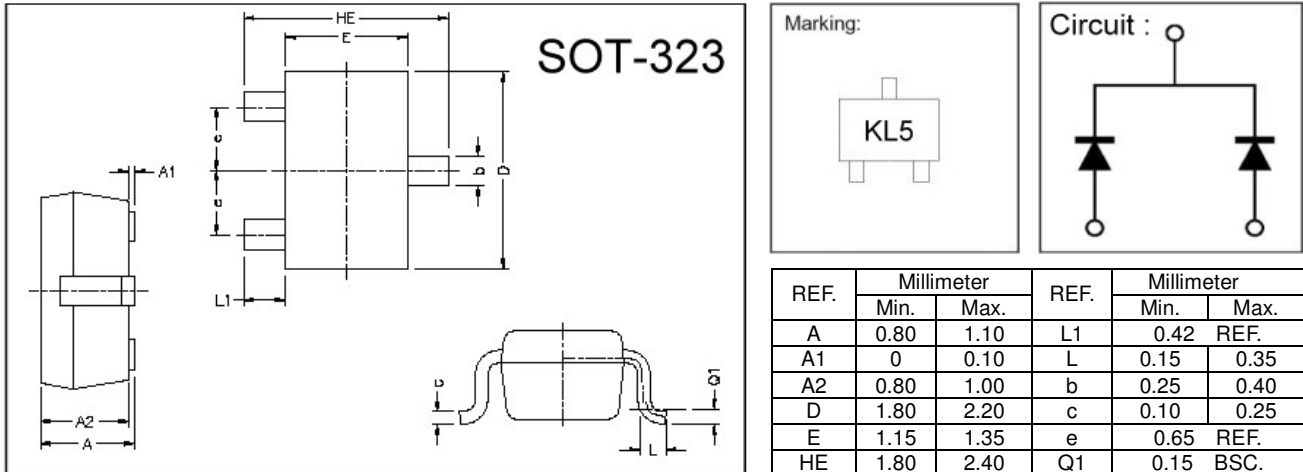
## GS705SD

**SURFACE MOUNT, SCHOTTKY BARRIER DIODE**  
**VOLTAGE 40V, CURRENT 0.03A**

### Description

The GS705SD is designed for general purpose detection and high speed switching.

### Package Dimensions



### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>J</sub>	+125	°C
Storage Temperature	T <sub>stg</sub>	-40 ~ +125	°C
Maximum Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	40	V
Maximum RMS Voltage	V <sub>RMS</sub>	28	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I <sub>FSM</sub>	0.2	A
Typical Junction Capacitance between Terminal (Note 1)	C <sub>J</sub>	2.0	pF
Maximum Average Forward Rectified Current	I <sub>o</sub>	0.03	A
Total Power Dissipation	PD	225	mW

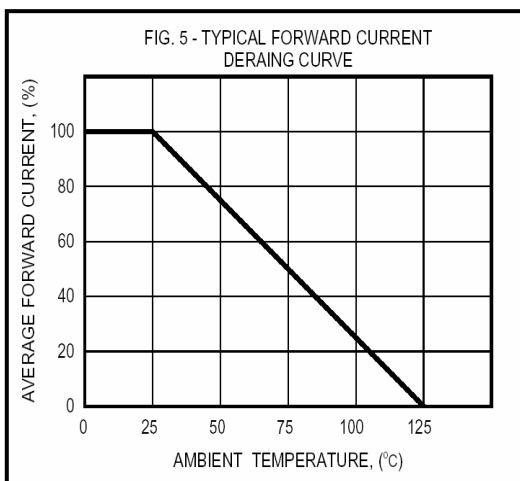
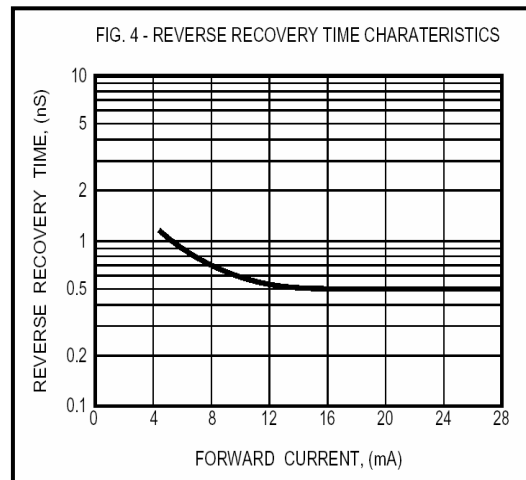
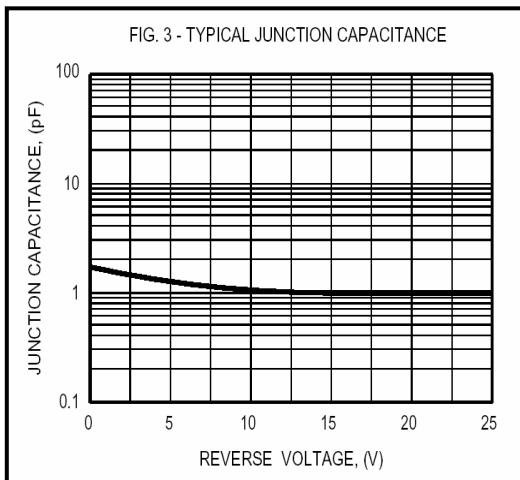
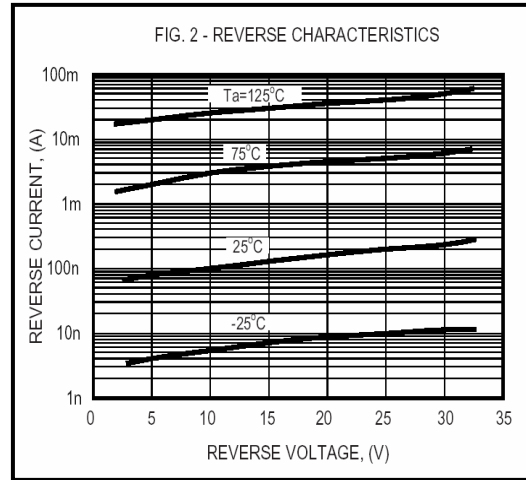
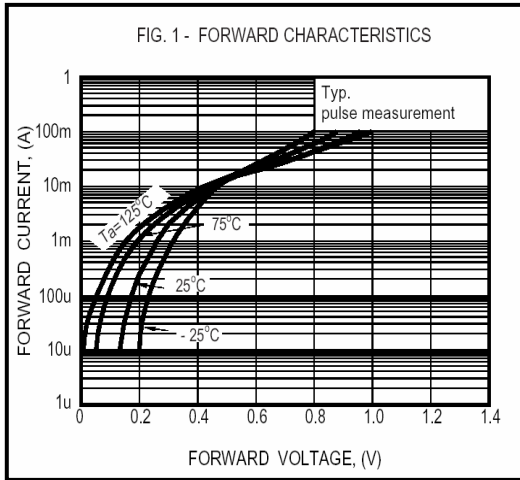
### Characteristics at Ta = 25°C

Characteristics	Symbol	Typ.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V <sub>F</sub>	0.37	V	IF = 1mA
Maximum Average Reverse Current	IR	1.0	uA	VR = 10V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 1.0 volt.

2. ESD sensitive product handling required.

## Characteristics Curve



**Important Notice:**

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

**Head Office And Factory:**

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165